RENESAS

ISL54047

NOT RECOMMENDED FOR NEW DESIGNS RECOMMENDED REPLACEMENT PART ISL54050



FN6503 Rev 0.00 May 31, 2007

Ultra Low ON-Resistance, High Off-Isolation, Single Supply, Diff SPST Analog Switch

The Intersil ISL54047 device is a low ON-resistance, low voltage, high off-isolation, bidirectional, differential single-pole/single-throw (SPST) analog switch. It was designed to operate from a single +1.65V to +4.5V supply. Targeted applications include battery powered equipment that benefit from low R_{ON} (0.44 Ω) and fast switching speeds (t_{ON} = 40ns, t_{OFF} = 35ns). The digital logic input is 1.8V logic-compatible when using a single +3V supply.

The ISL54047 has been designed with a T-switch architecture. This approach results in maximum off-isolation while retaining a low impedance signal path when switches are ON.

The device can be used as a low impedance bypass element for noisy amplifier circuits.

The ISL54047 has two normally open (NO) SPST switches that are controlled by a single logic control pin.

TABLE 1. FEATURES AT A GLANCE

	ISL54047			
Number of Switches	2			
SW	SPST			
4.3V R _{ON}	0.44Ω			
4.3V t _{ON} /t _{OFF}	4.3V t _{ON} /t _{OFF} 40ns/35ns			
3V R _{ON}	0.51Ω			
3V t _{ON} /t _{OFF}	50ns/40ns			
1.8V R _{ON}	0.98Ω			
1.8V t _{ON} /t _{OFF}	70ns/65ns			
Package	10 Ld 1.8 x 1.4 x 0.5mm μTQFN			

Related Literature

- Technical Brief TB363 "Guidelines for Handling and Processing Moisture Sensitive Surface Mount Devices (SMDs)"
- Application Note AN557 "Recommended Test Procedures for Analog Switches"

Features

 T-Switch Architecture OFF-Isolation at 100kHz Into 50Ω Load
 ON Resistance (R_{ON}) V+ = +4.3V
+ R _{ON} Matching Between Channels0.04 Ω
• R _{ON} Flatness Across Signal Range0.07 Ω
Single Supply Operation+1.65V to +4.5V
+ Low Power Consumption (PD)
 Fast Switching Action (V+ = +4.3V) t_{ON}
• ESD HBM Rating>8kV
 1.8V Logic Compatible (+3V supply)

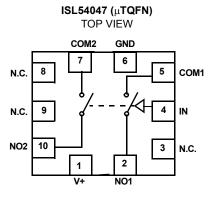
- · Low ICC Current when VinH is not at the V+ Raill
- Available in 10 lead 1.8 x 1.4 x 0.5mm μ TQFN
- Pb-Free Plus Anneal Available (RoHS Compliant)

Applications

- Battery powered, Handheld, and Portable Equipment
 - Cellular/mobile Phones
 - Pagers
 - Laptops, Notebooks, Palmtops
- Portable Test and Measurement
- · Medical Equipment
- · Audio and Video Switching



Pinout (Note 1)



NOTE:

1. Switches Shown for Logic "0" Input.

Truth Table

LOGIC	NO1, NO2
0	OFF
1	ON

NOTE: Logic "0" ${\leq}0.5V.$ Logic "1" ${\geq}1.4V$ with a 3V supply.

Pin Descriptions

PIN	FUNCTION
V+	System Power Supply Input (+1.65V to +4.5V)
GND	Ground Connection
IN	Digital Control Input
COMx	Analog Switch Common Pin
NOx	Analog Switch Normally Open Pin
N.C.	No Connect

Ordering Information

PART NUMBER (Note)	PART MARKING	TEMP. RANGE (°C)	PACKAGE (Pb-Free)	PKG. DWG. #
ISL54047IRUZ-T	D	-40 to +85	10 Ld 1.8 x 1.4 x 0.5mm $\mu TQFN$ Tape and Reel	L10.1.8x1.4A

NOTE: Intersil Pb-free products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020C.

Absolute Maximum Ratings

V+ to GND
Input Voltages
NO, IN (Note 2)
Output Voltages
COM (Note 2)
Continuous Current NO, COM ±300mA
Peak Current NO, COM
(Pulsed 1ms, 10% Duty Cycle, Max) ±500mA
ESD Rating:
HBM
MM
CDM>1.4kV

Thermal Information

Thermal Resistance (Typical)	θ _{JA} (°C/W)	θ _{JC} (°C/W)		
10 Ld μ TQFN Package (Note 3)	143	61		
Maximum Junction Temperature (Plastic F	Package)	+150°C		
Maximum Storage Temperature Range				
Pb-free reflow profile		ee link below		
http://www.intersil.com/pbfree/Pb-FreeR	Reflow.asp			

Operating Conditions

Temperature Range	-40°C to +85°C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. Extended operation above the recommended operating conditions could result in decreased reliability. The Absolute Maximum Ratings are stress only ratings and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTES:

2. Signals on NOx, IN, or COMx pins exceeding V+ or GND are clamped by internal diodes. Limit forward diode current to maximum current ratings.

3. θ_{JA} is measured with the component mounted on a high effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

Electrical Specifications - 4.3V Supply Test Conditions: V+ = +3.9V to +4.5V, GND = 0V, V_{INH} = 1.6V, V_{INL} = 0.5V (Note 4), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERIS	STICS					
Analog Signal Range, V _{ANALOG}		Full	0	-	V+	V
ON Resistance, R _{ON}	$V_{+} = 3.9V, I_{COM} = 100mA, V_{NO} = 0V \text{ to } V_{+},$	25	-	0.45	-	Ω
	(See Figure 4)	Full	-	0.55	-	Ω
R _{ON} Matching Between Channels,	V+ = 3.9V, I_{COM} = 100mA, V_{NO} = Voltage at max R_{ON} ,	25	-	0.04	-	Ω
ΔR_{ON}	(Note 7)	Full	-	0.04	-	Ω
R _{ON} Flatness, R _{FLAT(ON)}	V+ = 3.9V, I _{COM} = 100mA, V _{NO} = 0V to V+, (Note 6)	25	-	0.07	-	Ω
		Full	-	0.08	-	Ω
NO OFF Leakage Current,	V+ = 4.5V, V _{COM} = 0.3V, 3V, V _{NO} = 3V, 0.3V	25	-100	-	100	nA
NO(OFF)		Full	-195	-	195	nA
COM ON Leakage Current,	V+ = 4.5V, V _{COM} = 0.3V, 3V, or V _{NO} = 0.3V, 3V, or Floating	25	-100	-	100	nA
ICOM(ON)		Full	-195	-	195	nA
DYNAMIC CHARACTERISTICS		I	1		-	
Turn-ON Time, t _{ON}	V+ = 3.9V, V_{NO} = 3.0V, R_L =50 Ω , C_L = 35pF, (See Figure 1)	25	-	40	-	ns
		Full	-	50	-	ns
Turn-OFF Time, t _{OFF}	V+ = 3.9V, V_{NO} = 3.0V, R_L =50 Ω , C_L = 35pF, (See Figure 1)	25	-	35	-	ns
		Full	-	45	-	ns
Charge Injection, Q	C_L = 1.0nF, V_G = 2V, R_G = 0 Ω , (See Figure 2)	25	-	192	-	рС
OFF Isolation	R_L = 50 Ω , C_L = 5pF, f = 100kHz, V_{COM} = 1 V_{RMS} , (See Figure 3)	25	-	102	-	dB
OFF Isolation	$R_L = 50\Omega$, $C_L = 5pF$, f = 1MHz, $V_{COM} = 1V_{RMS}$, (See Figure 3)	25	-	81	-	dB
Crosstalk (Channel-to-Channel)	R_L = 50 Ω , C_L = 5pF, f = 1MHz, V_{COM} = 1 V_{RMS} , (See Figure 5)	25	-	-95	-	dB
Total Harmonic Distortion	f = 20Hz to 20kHz, V_{COM} = 2 V_{P-P} , R_L = 600 Ω	25	-	0.01	-	%



Electrical Specifications - 4.3V Supply

Test Conditions: V+ = +3.9V to +4.5V, GND = 0V, V_{INH} = 1.6V, V_{INL} = 0.5V (Note 4), Unless Otherwise Specified **(Continued)**

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
NO OFF Capacitance, C _{OFF}	f = 1MHz, $V_{NO} = V_{COM} = 0V$, (See Figure 6)	25	-	46	-	pF
COM ON Capacitance, C _{COM(ON)}	f = 1MHz, $V_{NO} = V_{COM} = 0V$, (See Figure 6)	25	-	233	-	pF
POWER SUPPLY CHARACTERIST	rics	W	<u> </u>			
Power Supply Range		Full	1.65		4.5	V
Positive Supply Current, I+	V+ = +4.5V, V _{IN} = 0V	25	-	-	0.1	μA
		Full	-	-	1	μA
Positive Supply Current, I+	V+ = +4.5V, V _{IN} = V+	25	-	-	0.5	μA
		Full	-	-	1	μA
Positive Supply Current, I+	V+ = +4.2V, V _{IN} = 2.85V	25	-	-	12	μA
DIGITAL INPUT CHARACTERISTI	cs		1			
Input Voltage Low, V _{INL}		Full	-	-	0.5	V
Input Voltage High, V _{INH}		Full	1.6	-	-	V
Input Current, I _{INH} , I _{INL}	V+ = 4.5V, V _{IN} = 0V or V+	Full	-0.5	-	0.5	μA

Electrical Specifications - 3V Supply

Test Conditions: V+ = +2.7V to +3.3V, GND = 0V, V_{INH} = 1.4V, V_{INL} = 0.5V (Note 4), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERIS	STICS		· · · · · · · · ·			•
Analog Signal Range, V _{ANALOG}		Full	0	-	V+	V
ON Resistance, R _{ON}	V+ = 2.7V, I _{COM} = 100mA, V _{NO} = 0V to V+,	25	-	0.55	0.6	Ω
	(See Figure 4)	Full	-	-	0.8	Ω
R _{ON} Matching Between Channels,	V+ = 2.7V, I_{COM} = 100mA, V_{NO} = Voltage at max R_{ON} ,	25	-	0.05	0.07	Ω
ΔR _{ON}	(Note 7)	Full	-	-	0.08	Ω
R _{ON} Flatness, R _{FLAT(ON)}	V+ = 2.7V, I _{COM} = 100mA, V _{NO} = 0V to V+, (Note 6)	25	-	0.1	0.15	Ω
		Full	-	-	0.15	Ω
NO OFF Leakage Current,	V+ = 3.3V, V _{COM} = 0.3V, 3V, V _{NO} = 3V, 0.3V	25	-	0.9	-	nA
I _{NO(OFF)}		Full	-	30	-	nA
COM ON Leakage Current,	V+ = 3.3V, V _{COM} = 0.3V, 3V, or V _{NO} = 0.3V, 3V, or	25	-	0.8	-	nA
ICOM(ON)	Floating	Full	-	30	-	nA
DYNAMIC CHARACTERISTICS					·	
Turn-ON Time, t _{ON}	V+ = 2.7V, V _{NO} = 1.5V, R _L = 50 Ω , C _L = 35pF, (See Figure 1)	25	-	50	-	ns
		Full	-	60	-	ns
Turn-OFF Time, t _{OFF}	V+ = 2.7V, V_{NO} = 1.5V, R_L = 50 Ω , C_L = 35pF,	25	-	40	-	ns
	(See Figure 1)	Full	-	50	-	ns
Charge Injection, Q	C_L = 1.0nF, V_G = 1.5V, R_G = 0 Ω , (See Figure 2)	25	-	115	-	рС
OFF Isolation	R_L = 50 Ω , C_L = 5pF, f = 100kHz, V_{COM} = 1 V_{RMS} , (See Figure 3)	25	-	102	-	dB
OFF Isolation	R_L = 50 Ω , C_L = 5pF, f = 1MHz, V_{COM} = 1 V_{RMS} , (See Figure 3)	25	-	81	-	dB
Crosstalk (Channel-to-Channel)	$R_L = 50\Omega$, $C_L = 5pF$, f = 1MHz, $V_{COM} = 1V_{RMS}$, (See Figure 5)	25	-	-95	-	dB



Electrical Specifications - 3V Supply

Test Conditions: V+ = +2.7V to +3.3V, GND = 0V, V_{INH} = 1.4V, V_{INL} = 0.5V (Note 4), Unless Otherwise Specified (Continued)

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
Total Harmonic Distortion	f = 20Hz to 20kHz, V_{COM} = 2 V_{P-P} , R_L = 600 Ω	25	-	0.016	-	%
NO Capacitance, C _{OFF}	f = 1MHz, V_{NO} = V_{COM} = 0V, (See Figure 6)	25	-	48	-	pF
COM ON Capacitance, C _{COM(ON)}	f = 1MHz, V_{NO} = V_{COM} = 0V, (See Figure 6)	25	-	236	-	pF
POWER SUPPLY CHARACTERIST	ICS					
Positive Supply Current, I+	V+ = +3.6V, V _{IN} = 0V or V+	25	-	0.01	-	μA
		Full	-	0.52	-	μA
DIGITAL INPUT CHARACTERISTIC	CS CS				1	
Input Voltage Low, VINL		25	-	-	0.5	V
Input Voltage High, V _{INH}		25	1.4	-	-	V
Input Current, I _{INH} , I _{INL}	V+ = 3.3V, V _{IN} = 0V or V+	Full	-0.5	-	0.5	μA

Electrical Specifications - 1.8V Supply

Test Conditions: V+ = +1.65V to +2V, GND = 0V, V_{INH} = 1.0V, V_{INL} = 0.4V (Note 4), Unless Otherwise Specified

PARAMETER	TEST CONDITIONS	TEMP (°C)	(NOTE 5) MIN	ТҮР	(NOTE 5) MAX	UNITS
ANALOG SWITCH CHARACTERIS	STICS					
Analog Signal Range, V _{ANALOG}	, V _{ANALOG}		0	-	V+	V
ON Resistance, R _{ON}	V+ = 1.65V, I _{COM} = 100mA, V _{NO} = 0V to V+,	25	-	1.24	-	Ω
	(See Figure 4)	Full	-	1.34	-	Ω
DYNAMIC CHARACTERISTICS		I				
Turn-ON Time, t _{ON}	V+ = 1.65V, V _{NO} = 1.0V, R _L =50 Ω , C _L = 35pF, (See Figure 1)	25	-	70	-	ns
		Full	-	80	-	ns
Turn-OFF Time, t _{OFF}	V+ = 1.65V, V _{NO} = 1.0V, R _L =50 Ω , C _L = 35pF, (See Figure 1)	25	-	65	-	ns
		Full	-	75	-	ns
Charge Injection, Q	C_L = 1.0nF, V_G = 1V, R_G = 0 Ω , (See Figure 2)	25	-	53	-	рС
NO OFF Capacitance, C _{OFF}	f = 1MHz, V _{NO} = V _{COM} = 0V, (See Figure 6)	25	-	52	-	pF
COM ON Capacitance, C _{COM(ON)}	f = 1MHz, V _{NO} = V _{COM} = 0V, (See Figure 6)	25	-	237	-	pF
DIGITAL INPUT CHARACTERISTI	CS					
Input Voltage Low, V _{INL}		25	-	-	0.4	V
Input Voltage High, V _{INH}		25	1.0	-	-	V
Input Current, I _{INH} , I _{INL}	V+ = 2.0V, V _{IN} = 0V or V+	Full	-0.5	-	0.5	μA

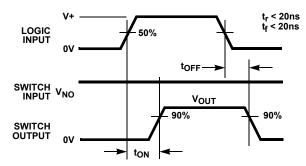
NOTES:

4. V_{IN} = input voltage to perform proper function.

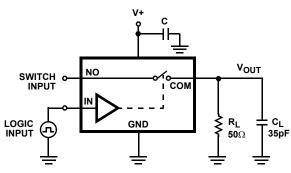
- 5. The algebraic convention, whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- 6. Flatness is defined as the difference between maximum and minimum value of on-resistance over the specified analog signal range.
- 7. R_{ON} matching between channels is calculated by subtracting the channel with the highest max Ron value from the channel with lowest max Ron value, between NO1 and NO2.



Test Circuits and Waveforms



Logic input waveform is inverted for switches that have the opposite logic sense.



Repeat test for all switches. CL includes fixture and stray capacitance.

$$V_{OUT} = V_{(NO)} \frac{R_L}{R_L + R_{(ON)}}$$

FIGURE 1B. TEST CIRCUIT



FIGURE 1. SWITCHING TIMES

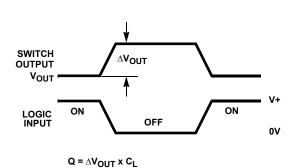
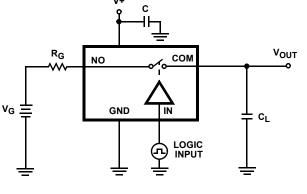


FIGURE 2A. MEASUREMENT POINTS



Repeat test for all switches.

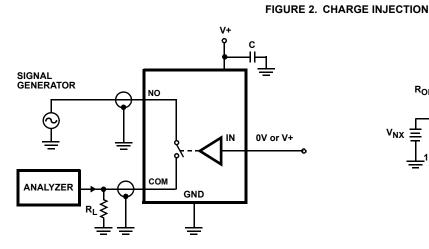
FIGURE 2B. TEST CIRCUIT

NO

сом

GND

V



Signal direction through switch is reversed, worst case values are recorded. Repeat test for all switches.

FIGURE 3. OFF ISOLATION TEST CIRCUIT

Repeat test for all switches.

100mA `♠

R_{ON} = V₁/100mA

V_{NX}

FIGURE 4. RON TEST CIRCUIT

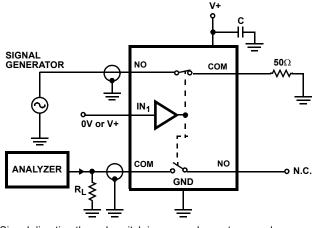
FN6503 Rev 0.00 May 31, 2007



0V or V+

IN

Test Circuits and Waveforms (Continued)



Signal direction through switch is reversed, worst case values are recorded. Repeat test for all switches.



Detailed Description

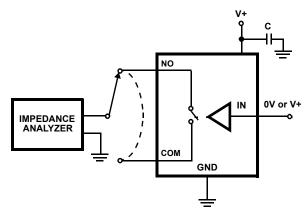
The ISL54047 is a bidirectional, differential single pole/single throw (SPST) analog switch that offer precise switching capability from a single 1.65V to 4.5V supply with low on-resistance (0.44 Ω) and high speed operation (t_{ON} = 40ns, t_{OFF} = 35ns). The devices are especially well suited for portable battery powered equipment due to their low operating supply voltage (1.65V), low power consumption (4.5 μ W max) and the tiny μ TQFN package. The ultra low on-resistance and Ron flatness provide very low insertion loss and distortion to applications that require signal reproduction.

External V+ Series Resistor

For improved ESD and latch-up immunity Intersil recommends adding a 100Ω resistor in series with the V+ power supply pin of the ISL54047 IC (see Figure 7).

During an over-voltage transient event, such as occurs during system level IEC 61000 ESD testing, substrate currents can be generated in the IC that can trigger parasitic SCR structures to turn ON, creating a low impedance path from the V+ power supply to ground. This will result in a significant amount of current flow in the IC which can potentially create a latch-up state or permanently damage the IC. The external V+ resistor limits the current during this over-stress situation and has been found to prevent latch-up or destructive damage for many over voltage transient events.

Under normal operation the sub-microamp I_{DD} current of the IC produces an insignificant voltage drop across the 100Ω series resistor resulting in no impact to switch operation or performance.



Repeat test for all switches.

FIGURE 6. CAPACITANCE TEST CIRCUIT

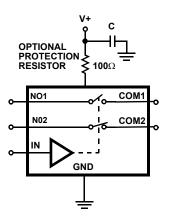


FIGURE 7. V+ SERIES RESISTOR FOR ENHANCED ESD AND LATCH-UP IMMUNITY

Supply Sequencing and Overvoltage Protection

With any CMOS device, proper power supply sequencing is required to protect the device from excessive input currents which might permanently damage the IC. All I/O pins contain ESD protection diodes from the pin to V+ and to GND (see Figure 8). To prevent forward biasing these diodes, V+ must be applied before any input signals, and the input signal voltages must remain between V+ and GND.

If these conditions cannot be guaranteed, then precautions must be implemented to prohibit the current and voltage at the logic pin and signal pins from exceeding the maximum ratings of the switch. The following two methods can be used to provided additional protection to limit the current in the event that the voltage at a signal pin or logic pin goes below ground or above the V+ rail.

Logic inputs can be protected by adding a $1k\Omega$ resistor in series with the logic input (see Figure 8). The resistor limits



the input current below the threshold that produces permanent damage, and the sub-microamp input current produces an insignificant voltage drop during normal operation.

This method is not acceptable for the signal path inputs. Adding a series resistor to the switch input defeats the purpose of using a low R_{ON} switch. Connecting schottky diodes to the signal pins as shown in Figure 8 will shunt the fault current to the supply or to ground thereby protecting the switch. These schottky diodes must be sized to handle the expected fault current.

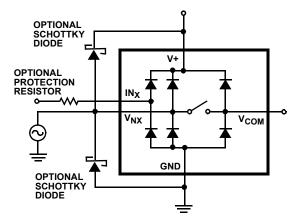


FIGURE 8. OVERVOLTAGE PROTECTION

Power-Supply Considerations

The ISL54047 construction is typical of most single supply CMOS analog switches, in that they have two supply pins: V+ and GND. V+ and GND drive the internal CMOS switches and set their analog voltage limits. Unlike switches with a 4V maximum supply voltage, the ISL54047 5.5V maximum supply voltage provides plenty of room for the 10% tolerance of 4.3V supplies, as well as room for overshoot and noise spikes.

The minimum recommended supply voltage is 1.65V. It is important to note that the input signal range, switching times, and on-resistance degrade at lower supply voltages. Refer to the Electrical Specification Tables on page 5 and Typical Performance Curves on page 9 for details.

V+ and GND also power the internal logic and level shifters. The level shifters convert the input logic levels to switched V+ and GND signals to drive the analog switch gate terminals.

This family of switches cannot be operated with bipolar supplies, because the input switching point becomes negative in this configuration.

Logic-Level Thresholds

This switch family are 1.8V CMOS compatible (0.5V and 1.4V) over a supply range of 2.7V to 4.5V (see Figure 18). At 2.7V the V_{IL} level is about 0.53V. This is still above the 1.8V CMOS guaranteed low output maximum level of 0.5V, but noise margin is reduced.

The digital input stages draw supply current whenever the digital input voltage is not at one of the supply rails. Driving the digital input signals from GND to V+ with a fast transition time minimizes power dissipation.

The ISL54047 has been designed to minimize the supply current whenever the digital input voltage is not driven to the supply rails (0V to V+). For example driving the device with 2.85V logic (0V to 2.85V) while operating with a 4.2V supply the device draws only 12μ A of current (see Figure 16 for VIN = 2.85V).

Frequency Performance

In 50 Ω systems, the ISL54047 has a -3dB bandwidth of 27MHz (see Figure 21). The frequency response is very consistent over a wide V+ range, and for varying analog signal levels.

An OFF switch acts like a capacitor and passes higher frequencies with less attenuation, resulting in signal feed through from a switch's input to its output. Off Isolation is the resistance to this feed through, while Crosstalk indicates the amount of feed through from one switch to another. Figure 22 details the high Off Isolation and Crosstalk rejection provided by this part. At 100kHz, Off Isolation is about 102dB in 50 Ω systems, 118dB into 8 Ω , and 124dB into 4 Ω , decreasing approximately 20dB per decade as frequency increases. Higher load impedances decrease Off Isolation and Crosstalk rejection due to the voltage divider action of the switch OFF impedance and the load impedance.

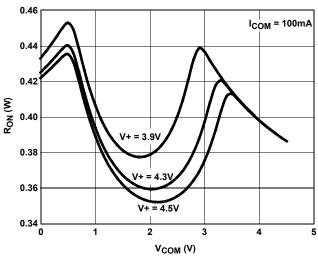
Leakage Considerations

Reverse ESD protection diodes are internally connected between each analog-signal pin and both V+ and GND. One of these diodes conducts if any analog signal exceeds V+ or GND.

Virtually all the analog leakage current comes from the ESD diodes to V+ or GND. Although the ESD diodes on a given signal pin are identical and therefore fairly well balanced, they are reverse biased differently. Each is biased by either V+ or GND and the analog signal. This means their leakages will vary as the signal varies. The difference in the two diode leakages to the V+ and GND pins constitutes the analog-signal-path leakage current. All analog leakage current flows between each pin and one of the supply terminals, not to the other switch terminal. This is why both sides of a given switch can show leakage currents of the same or opposite polarity. There is no connection between the analog signal paths and V+ or GND.



Typical Performance Curves T_A = 25 °C, Unless Otherwise Specified





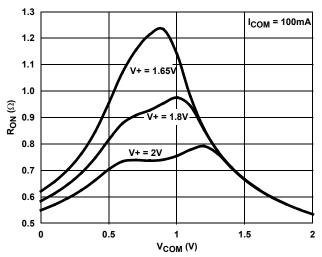
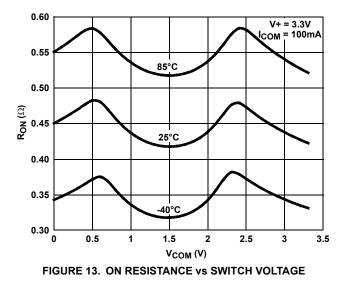


FIGURE 11. ON RESISTANCE vs SUPPLY VOLTAGE vs SWITCH VOLTAGE



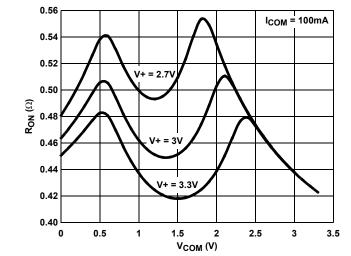
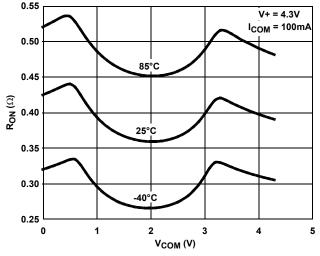
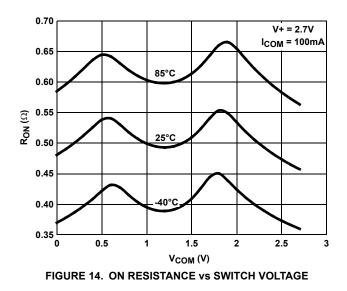


FIGURE 10. ON RESISTANCE vs SUPPLY VOLTAGE vs SWITCH VOLTAGE







FN6503 Rev 0.00 May 31, 2007



Typical Performance Curves T_A = 25 °C, Unless Otherwise Specified (Continued)

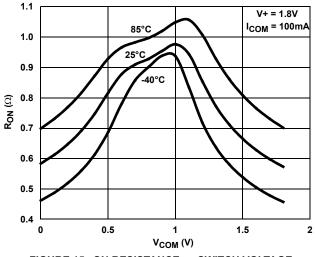


FIGURE 15. ON RESISTANCE vs SWITCH VOLTAGE

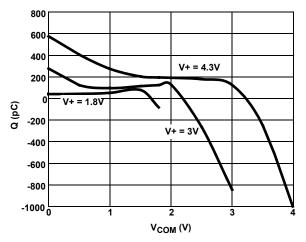


FIGURE 17. CHARGE INJECTION vs SWITCH VOLTAGE

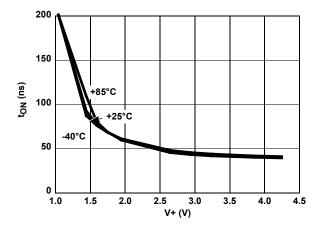


FIGURE 19. TURN-ON TIME vs SUPPLY VOLTAGE

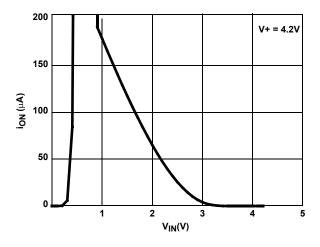


FIGURE 16. SUPPLY CURRENT vs VLOGIC VOLTAGE

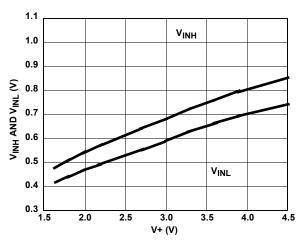


FIGURE 18. DIGITAL SWITCHING POINT vs SUPPLY VOLTAGE

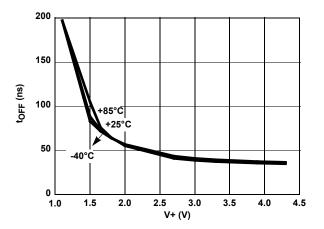
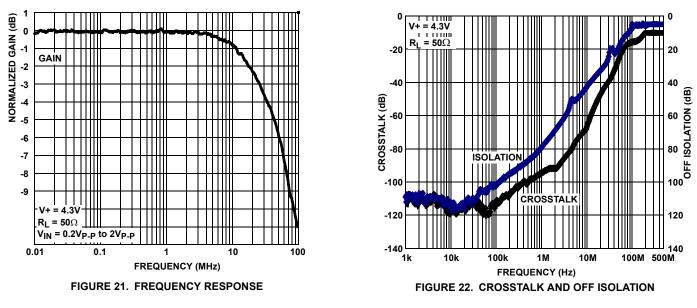


FIGURE 20. TURN-OFF TIME vs SUPPLY VOLTAGE

Typical Performance Curves T_A = 25 °C, Unless Otherwise Specified (Continued)



Die Characteristics

SUBSTRATE POTENTIAL (POWERED UP):

GND

TRANSISTOR COUNT:

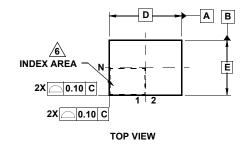
114

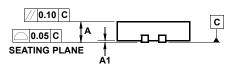
PROCESS:

Submicron CMOS

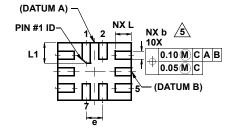


Ultra Thin Quad Flat No-Lead Plastic Package (UTQFN)

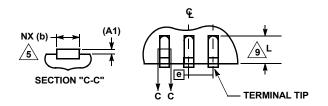




SIDE VIEW



BOTTOM VIEW



L10.1.8x1.4A

10 LEAD ULTRA THIN QUAD FLAT NO-LEAD PLASTIC PACKAGE

	N			
SYMBOL	MIN	NOMINAL	MAX	NOTES
А	0.45	0.50	0.55	-
A1	-	-	0.05	-
A3	0.1	-		
b	0.15	0.20	0.25	5, 9
D	1.75	1.80	1.85	-
E	1.35	1.40	1.45	-
е	0.40 BSC			-
L	0.35	0.40	0.45	9
L1	0.45	0.50	0.55	-
Ν	10			2
Nd		3		
Ne	3			3
θ	0	- 12		4

NOTES:

Rev. 1 1/06

- 1. Dimensioning and tolerancing conform to ASME Y14.5-1994.
- 2. N is the number of terminals.
- 3. Nd and Ne refer to the number of terminals on D and E side, respectively.
- 4. All dimensions are in millimeters. Angles are in degrees.
- 5. Dimension b applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.
- The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.
- 7. Maximum package warpage is 0.05mm.
- 8. Maximum allowable burrs is 0.076mm in all directions.
- Nominal dimensions are provided to assist with PCB Land Pattern Design efforts, see Intersil Technical Brief TB389.
- 10. JEDEC Reference MO-255.

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